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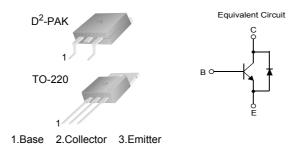
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FAIRCHILD SEMICONDUCTOR®

## KSC5338D/KSC5338DW NPN Triple Diffused Planar Silicon Transistor

## Features

- High Voltage Power Switch Switching Application
- Wide Safe Operating Area
- Built-in Free-Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time
- Two Package Choices : TO-220 or D<sup>2</sup>-PAK



### Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

| Symbol           | Parameter                                | Value       | Units |
|------------------|--|-------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage                   | 1000        | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage                | 450         | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage                     | 12          | V     |
| Ι <sub>C</sub>   | Collector Current (DC)                   | 5           | A     |
| I <sub>CP</sub>  | *Collector Current (Pulse)               | 10          | Α     |
| Ι <sub>Β</sub>   | Base Current (DC)                        | 2           | А     |
| I <sub>BP</sub>  | *Base Current (Pulse)                    | 4           | А     |
| P <sub>C</sub>   | Power Dissipation (T <sub>C</sub> =25°C) | 75          | W     |
| TJ               | Junction Temperature                     | 150         | °C    |
| T <sub>STG</sub> | Storage Temperature                      | - 55 to 150 | °C    |

\* Pulse Test : Pulse Width = 5ms, Duty Cycle  $\leq$  10%

## **Thermal Characteristics**

| Symbol           | Parameter              |                     | Rating | Units |
|------------------|------------------------|---------------------|--------|-------|
| R <sub>θjc</sub> | - Thermal Resistance   | Junction to Case    | 1.65   | °C/W  |
| R <sub>θja</sub> |                        | Junction to Ambient | 62.5   | °C/W  |
| Τ <sub>L</sub>   | Maximum Lead Temperatu | re for Soldering    | 270    | °C    |

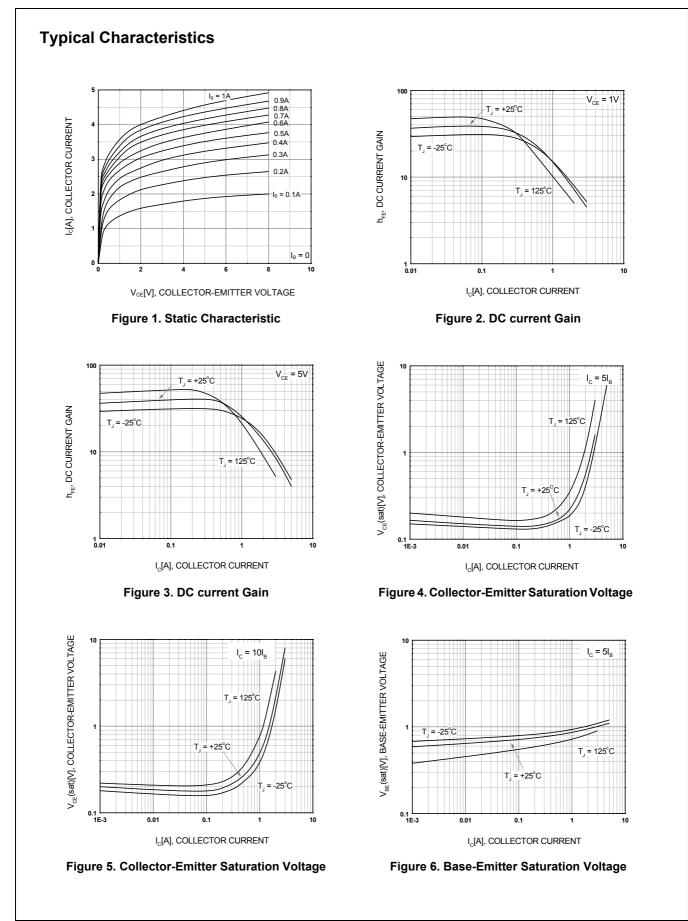
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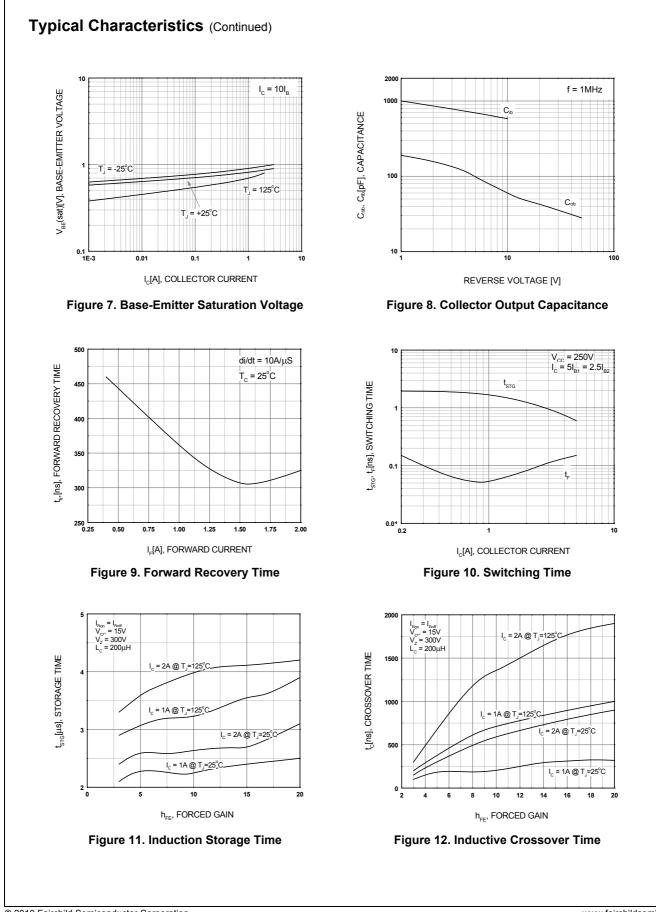
May 2010

| Symbol                | Parameter                            | Test Cond   | ition                 | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|-----------------------|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | I <sub>C</sub> =1mA, I <sub>E</sub> =0                                      |                       | 1000 |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  |   |                       | 450  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =1mA, I <sub>C</sub> =0                                      |                       | 12   |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =800V, I <sub>E</sub> =0                                    |                       |      |      | 10   | μA    |
| I <sub>CES</sub>      | Collector Cut-off Current            | V <sub>CES</sub> =1000V, I <sub>EB</sub> =0                                 | T <sub>a</sub> =25°C  |      |      | 100  | μΑ    |
| 020                   |                                      |   | T <sub>a</sub> =125°C |      |      | 500  | μΑ    |
| I <sub>CEO</sub>      | Collector Cut-off Current            | V <sub>CE</sub> =450V, I <sub>B</sub> =0                                    | T <sub>a</sub> =25°C  |      |      | 100  | μA    |
| 020                   |                                      |   | T <sub>a</sub> =125°C |      |      | 500  | μA    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | V <sub>EB</sub> =10V, I <sub>C</sub> =0                                     | u                     |      |      | 10   | μA    |
| h <sub>FE</sub>       | DC Current Gain                      | V <sub>CE</sub> =1V, I <sub>C</sub> =0.8A                                   | T <sub>a</sub> =25°C  | 15   | 25   |      |       |
| . –                   |                                      |   |                       | 10   | 14   |      |       |
|                       |                                      | V <sub>CE</sub> =1V, I <sub>C</sub> =2A                                     | T <sub>a</sub> =25°C  | 6    | 9    |      |       |
|                       |                                      | OL / O  |                       | 4    | 6    |      |       |
|                       |                                      | V <sub>CE</sub> =2.5V, I <sub>C</sub> =1A                                   | T <sub>a</sub> =25°C  | 18   | 25   |      |       |
|                       |                                      |   | T <sub>a</sub> =125°C | 14   | 18   |      |       |
| V <sub>CF</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =0.8A, I <sub>B</sub> =0.08A                                 | T <sub>a</sub> =25°C  |      | 0.35 | 0.5  | V     |
| OL(11)                |                                      |   | T <sub>a</sub> =125°C |      | 0.55 | 0.75 | V     |
|                       |                                      | I <sub>C</sub> =2A, I <sub>B</sub> =0.4A                                    | T <sub>a</sub> =25°C  |      | 0.47 | 0.75 | V     |
|                       |                                      |   | T <sub>a</sub> =125°C |      | 0.9  | 1.1  | V     |
|                       |                                      | I <sub>C</sub> =0.8A, I <sub>B</sub> =0.04A                                 |                       |      | 0.9  | 1.5  | V     |
|                       |                                      |   | T <sub>a</sub> =125°C |      | 1.8  | 2.5  | V     |
|                       |                                      | I <sub>C</sub> =1A, I <sub>B</sub> =0.2A                                    | T <sub>a</sub> =25°C  |      | 0.22 | 0.5  | v     |
|                       |                                      | .С. н., .В. с. <u>–</u> . с   | T <sub>a</sub> =125°C |      | 0.3  | 0.6  | V     |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> =0.8A, I <sub>B</sub> =0.08A                                 | T <sub>a</sub> =25°C  |      | 0.8  | 1.0  | V     |
| BE(out)               |                                      |   | T <sub>a</sub> =125°C |      | 0.65 | 0.9  | V     |
|                       |                                      | I <sub>C</sub> =2A, I <sub>B</sub> =0.4A                                    | T <sub>a</sub> =25°C  |      | 0.9  | 1.0  | V     |
|                       |                                      | 1C 27 (, 1B 0.17 (  | T <sub>a</sub> =125°C |      | 0.8  | 0.9  | v     |
| C <sub>ib</sub>       | Input Capacitance                    | V <sub>EB</sub> =10V, I <sub>C</sub> =0.5A,                                 | ŭ                     |      | 550  | 750  | pF    |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1                                |                       |      | 60   | 100  | pF    |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | I <sub>C</sub> =0.5A,V <sub>CE</sub> =10V                                   |                       |      | 11   | 100  | MHz   |
| V <sub>F</sub>        | Diode Forward Voltage                | I <sub>F</sub> =1A, I <sub>C</sub> =1mA,                                    | T <sub>a</sub> =25°C  |      | 0.86 | 1.3  | V     |
| ۷F                    | blode i of ward voltage              | I <sub>E</sub> =0   | T <sub>a</sub> =125°C |      | 0.79 | 1.0  | v     |
|                       |                                      | I <sub>F</sub> =2A  | T <sub>a</sub> =25°C  |      | 0.95 | 1.5  | V     |
|                       |                                      |   | T <sub>a</sub> =125°C |      | 0.88 | 1.0  | V     |
| t <sub>fr</sub>       | Diode Forward Recovery Time          | I <sub>F</sub> =0.4A  | 1a-120 0              |      | 460  |      | ns    |
| ٩r                    | (di/dt=10A/µs)                       | I <sub>F</sub> =1A  |                       |      | 360  |      | ns    |
|                       |                                      | I <sub>F</sub> =2A  |                       |      | 325  |      | ns    |
| CE(DSAT)              | Dynamic Saturation Voltage           | I <sub>C</sub> =1A, I <sub>B1</sub> =100mA<br>V <sub>CC</sub> =300V at 1 μs | T <sub>a</sub> =25°C  |      | 8    |      | V     |
|                       |                                      |   | T <sub>a</sub> =125°C |      | 15   |      | V     |
|                       |                                      | I <sub>C</sub> =1A, I <sub>B1</sub> =100mA                                  | T <sub>a</sub> =25°C  |      | 2.9  |      | V     |
|                       |                                      | $V_{CC}$ =300V at 3 µs  | T <sub>a</sub> =125°C |      | 8    |      | V     |
|                       |                                      | I <sub>C</sub> =2A, I <sub>B1</sub> =400mA<br>V <sub>CC</sub> =300V at 1 μs | T <sub>a</sub> =25°C  |      | 9    |      | V     |
|                       |                                      |   | T <sub>a</sub> =125°C |      | 17   |      | V     |
|                       |                                      | I <sub>C</sub> =2A, I <sub>B1</sub> =400mA                                  | T <sub>a</sub> =25°C  |      | 1.9  |      | V     |
|                       |                                      | $V_{CC}$ =300V at 3 µs  |                       | 1    | 8.5  | 1    | V     |

| KSC5338D/KSC5338DW                            |
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| - NPN Ti                                      |
| Triple  |
| e Diffused                                    |
| Planar  |
| Silicon                                       |
| NPN Triple Diffused Planar Silicon Transistor |

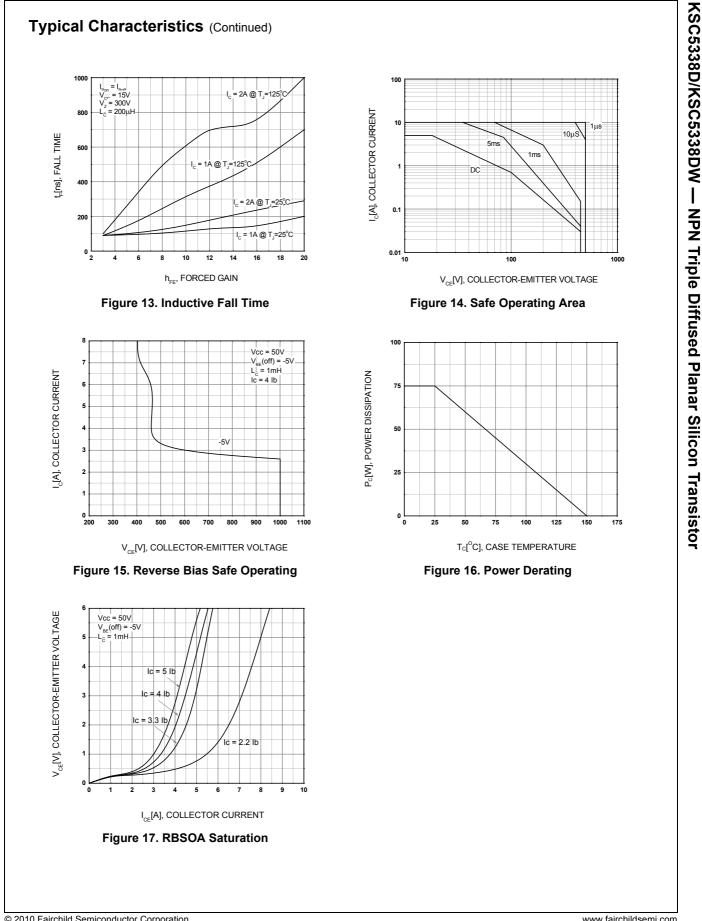
| Symbol           | Parameter                             | Test Co   | ndition                                       | Min  | Тур. | Max. | Units |
|------------------|---------------------------------------|---|---|------|------|------|-------|
| ESISTIVE         | LOAD SWITCHING (D.C < 10%             | , Pulse Width=40µs)                             |   |      |      |      | 1     |
| t <sub>ON</sub>  | Turn On Time                          | I <sub>C</sub> =2.5A, I <sub>B1</sub> =50       | 0mA,  |      | 500  | 750  | ns    |
| t <sub>STG</sub> | Storage Time                          | I <sub>B2</sub> =-1A, V <sub>CC</sub> =2        | 50V, R <sub>L</sub> = 100Ω                    | 1.2  |      | 1.5  | μS    |
| t <sub>F</sub>   | Fall Time                             |   | -   |      | 100  | 200  | ns    |
| t <sub>ON</sub>  | Turn On Time                          | I <sub>C</sub> =2A,                             | T <sub>a</sub> =25℃                           |      | 100  | 150  | ns    |
| 011              |                                       | I <sub>B1</sub> =400mA,                         | T <sub>a</sub> =125°C                         |      | 150  |      | ns    |
| t <sub>STG</sub> | Storage Time                          | I <sub>B2</sub> =-1A,                           | T <sub>a</sub> =25℃                           |      | 1.4  | 2.2  | μS    |
| 010              |                                       | V <sub>CC</sub> =300V,<br>R <sub>I</sub> = 150Ω | T <sub>a</sub> =125°C                         |      | 1.7  |      | μs    |
| t <sub>F</sub>   | Fall Time                             |   | T <sub>a</sub> =25℃                           |      | 90   | 150  | ns    |
| ·                |                                       |   | T <sub>a</sub> =125°C                         |      | 150  |      | ns    |
| t <sub>ON</sub>  | Turn On Time                          | I <sub>C</sub> =2.5A,                           | T <sub>a</sub> =25°C                          |      | 120  | 150  | ns    |
| 0N               |                                       | I <sub>B1</sub> =500mA,                         | T <sub>a</sub> =125°C                         |      | 150  |      | ns    |
| t <sub>STG</sub> | Storage Time                          | I <sub>B2</sub> =-5mA,                          | T <sub>a</sub> =25℃                           | 1.8  |      | 2.1  | μS    |
| 010              |                                       | V <sub>CC</sub> =300V,<br>R <sub>I</sub> = 120Ω | T <sub>a</sub> =125℃                          |      | 2.6  |      | μS    |
| t <sub>F</sub>   | Fall Time                             | 1(1 = 12022                                     | T <sub>a</sub> =25°C                          |      | 110  | 150  | ns    |
| 1                |                                       |   | T <sub>a</sub> =125°C                         |      | 160  |      | ns    |
| NDUCTIVE         | LOAD SWITCHING (V <sub>CC</sub> =15V) |   | a   |      |      |      |       |
| t <sub>STG</sub> | Storage Time                          | I <sub>C</sub> =2.5A,                           | T <sub>a</sub> =25℃                           |      | 1.9  | 2.2  | μS    |
| 010              |                                       | I <sub>B1</sub> =500mA,                         |   |      | 2.4  |      | μS    |
| t <sub>F</sub>   | Fall Time                             | I <sub>B2</sub> =-0.5A,                         | T <sub>a</sub> =25°C                          |      | 160  | 200  | ns    |
| 1                |                                       | V <sub>Z</sub> =350V,<br>L <sub>C</sub> =300μH  | T <sub>a</sub> =125°C                         |      | 330  |      | ns    |
| t <sub>C</sub>   | Cross-over Time                       | Ες=300μΠ  | T <sub>a</sub> =25°C                          |      | 350  | 500  | ns    |
| -0               |                                       |   | T <sub>a</sub> =125°C                         |      | 750  |      | ns    |
| t <sub>STG</sub> | Storage Time                          | I <sub>C</sub> =2A,                             | T <sub>a</sub> =25°C                          | 1.95 |      | 2.25 | μS    |
| -316             |                                       | I <sub>B1</sub> =400mA,                         | T <sub>a</sub> =125°C                         |      | 2.9  |      | μS    |
| t⊨               | Fall Time                             | I <sub>B2</sub> =-0.4A,                         | T <sub>a</sub> =25°C                          |      | 120  | 150  | ns    |
| 4                |                                       | V <sub>Z</sub> =300V,<br>L <sub>C</sub> =200μH  | T <sub>a</sub> =125°C                         |      | 270  |      | ns    |
| t <sub>C</sub>   | Cross-over Time                       | ις-200μπ  | T <sub>a</sub> =25°C                          |      | 300  | 450  | ns    |
| -0               |                                       |   | T <sub>a</sub> =125°C                         |      | 700  |      | ns    |
| t <sub>STG</sub> | Storage Time                          | I <sub>C</sub> =1A,                             | T <sub>a</sub> =25°C                          |      | 0.6  | 0.8  | μS    |
| -316             |                                       | I <sub>B1</sub> =100mA,                         | T <sub>a</sub> =125°C                         |      | 1.0  |      | μο    |
| t <sub>F</sub>   | Fall Time                             | I <sub>B2</sub> =-0.5A,                         | T <sub>a</sub> =25°C                          |      | 70   |      | ns    |
| Ŧ                |                                       | V <sub>Z</sub> =300V,                           | T <sub>a</sub> =125°C                         |      | 110  |      | ns    |
| t <sub>C</sub>   | Cross-over Time                       | L <sub>C</sub> =200μΗ                           | T <sub>a</sub> =25°C                          |      | 80   | 130  | ns    |
| •U               |                                       |   | T <sub>a</sub> =25 ℃<br>T <sub>a</sub> =125°C |      | 170  |      | ns    |



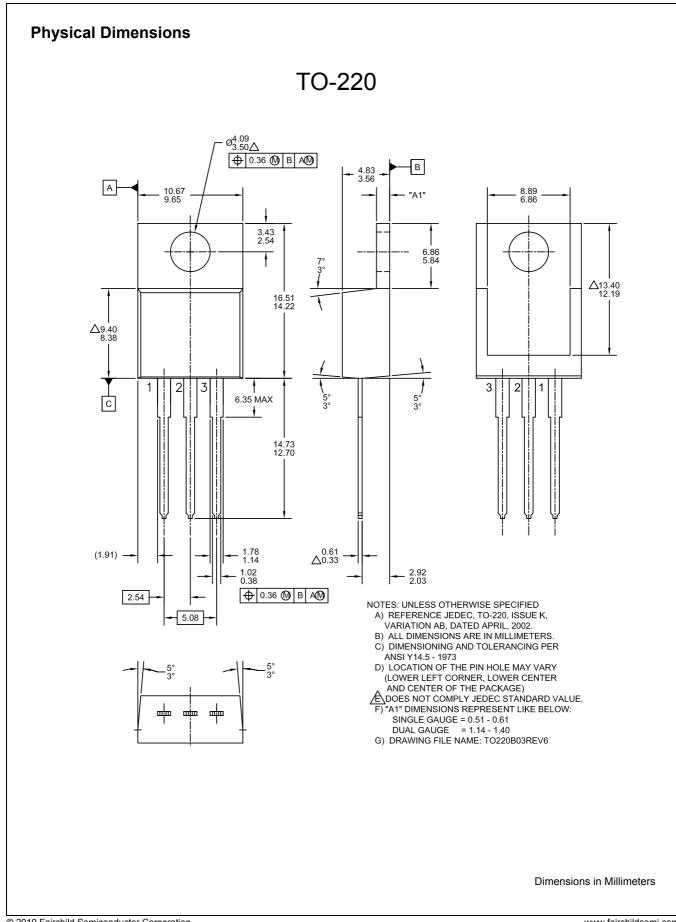


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7

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